

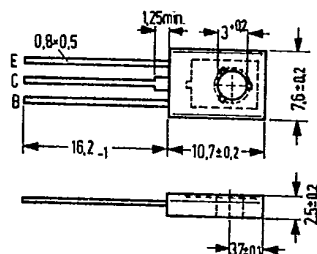
25C D ■ 8235605 0004346 4 ■ SIEG
NPN Silicon Planar Transistor

BD 329

SIEMENS AKTIENGESELLSCHAFT 25C 04346 D T-33-07

BD 329 is an epitaxial NPN silicon planar transistor in TO 126 plastic package (12 A 3 DIN 41 869, sheet 4). Together with its complementary transistor BD 330 it is particularly suitable for use in complementary output stages of medium performance (e.g. car radios).

Type	Ordering code
BD 329	Q62702-D394
BD 329/BD 330 paired	Q62702-D401
Spring washer A 3 DIN 137	Q62902-B63



Approx. weight 0.5 g Dimensions in mm
Transistor fixing with M3 screw
Starting torque max. 0.8 Nm
Washer or spring washer should be used.

Maximum ratings

Collector-emitter voltage
Collector-emitter voltage
Emitter-base voltage
Collector current
Emitter current
Base current
Junction temperature
Storage temperature range
Total power dissipation ($T_{amb} = 25^{\circ}\text{C}$)

V_{CES}	32	V
V_{CEO}	20	V
V_{EBO}	5	V
I_C	3	A
I_E	3	A
I_B	1	A
T_j	150	$^{\circ}\text{C}$
T_{stg}	-55 to +150	$^{\circ}\text{C}$
P_{tot}	15	W

Thermal resistance

Junction to ambient air
Junction to mounting area

R_{thJU}	≤ 100	K/W
R_{thJC}	≤ 7	K/W

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Static characteristics ($T_{amb} = 25^\circ\text{C}$)

Collector-emitter saturation voltage

($I_C = 2\text{ A}$; $I_B = 200\text{ mA}$)

Collector cutoff current

($V_{CB} = 32\text{ V}$)

Collector cutoff current

($V_{CB} = 32\text{ V}$; $T_j = 150^\circ\text{C}$)

Emitter cutoff current

($V_{EB} = 5\text{ V}$)

Base-emitter voltage

($V_{CE} = 10\text{ V}$; $I_C = 5\text{ mA}$)

($V_{CE} = 1\text{ V}$; $I_C = 2\text{ A}$)

DC current gain

$V_{CE} = 10\text{ V}$; $I_C = 5\text{ mA}$

$V_{CE} = 1\text{ V}$; $I_C = 0.5\text{ A}$

$V_{CE} = 1\text{ V}$; $I_C = 2\text{ A}$

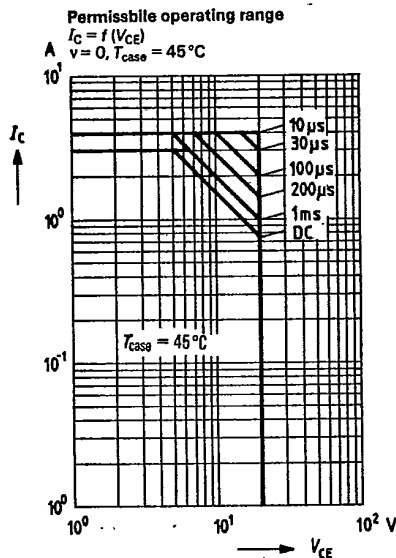
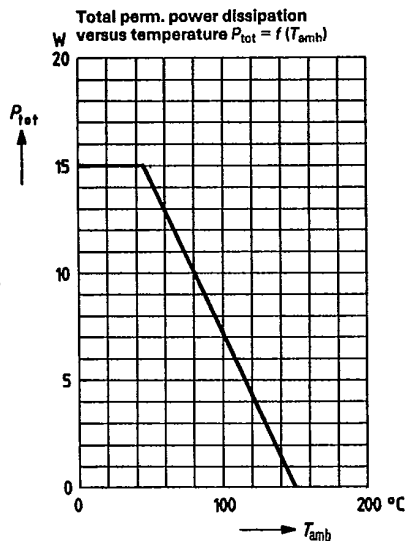
V_{CEsat}	≤ 0.5	V
I_{CBO}	≤ 10	μA
I_{CBO}	≤ 1	mA
I_{EBO}	≤ 10	μA
V_{BE}	0.6	V
V_{BE}	≤ 1.2	V
h_{FE}	> 50	—
h_{FE}	85 to 375	—
h_{FE}	> 40	—

Dynamic characteristics ($T_{amb} = 25^\circ\text{C}$)

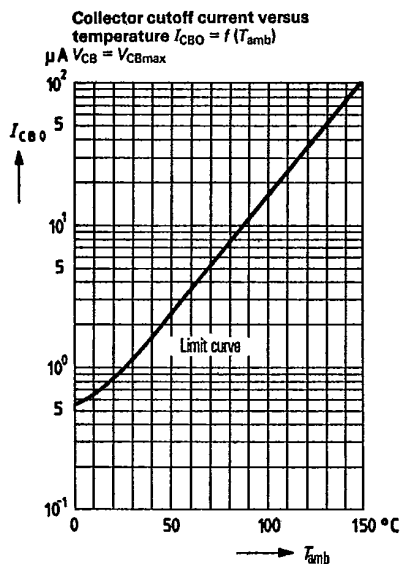
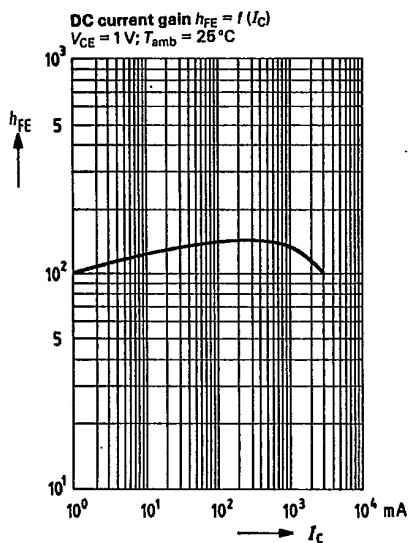
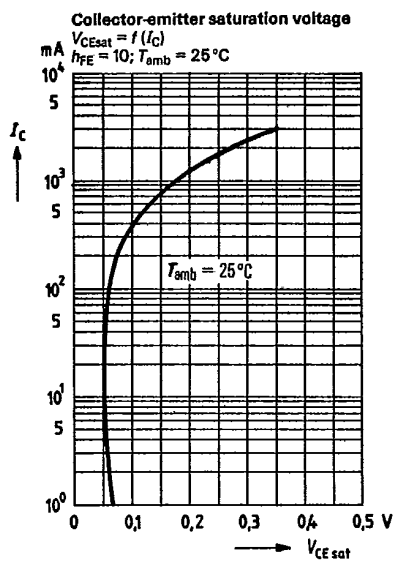
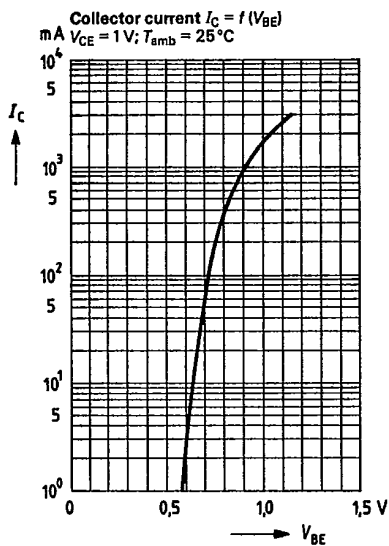
Transition frequency

($V_{CE} = 5\text{ V}$; $I_C = 50\text{ mA}$)

f_T	130	MHz
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This datasheet has been download from:

www.datasheetcatalog.com

Datasheets for electronics components.